

AMENDMENT TRANSMITTAL LETTER (Large Entity)Applicant(s): **Katsuhito Sasaki**

Docket No.

OKI.295Serial No.
10/052,244Filing Date
January 23, 2002Examiner
J. GarciaGroup Art Unit
2823Invention: **METHOD OF MANUFACTURING LATERAL DOUBLE-DIFFUSED METAL OXIDE
SEMICONDUCTOR DEVICE****TO THE ASSISTANT COMMISSIONER FOR PATENTS:**

Transmitted herewith is an amendment in the above-identified application.

The fee has been calculated and is transmitted as shown below.

CLAIMS AS AMENDED

	CLAIMS REMAINING AFTER AMENDMENT	HIGHEST # PREV. PAID FOR	NUMBER EXTRA CLAIMS PRESENT	RATE	ADDITIONAL FEE
TOTAL CLAIMS	18 -	20 =	0 x	\$18.00	\$0.00
INDEP. CLAIMS	3 -	3 =	0 x	\$84.00	\$0.00
Multiple Dependent Claims (check if applicable) <input type="checkbox"/>					\$0.00
TOTAL ADDITIONAL FEE FOR THIS AMENDMENT					\$0.00

- ☒ No additional fee is required for amendment.
- ☐ Please charge Deposit Account No. _____ in the amount of _____
A duplicate copy of this sheet is enclosed.
- ☐ A check in the amount of _____ to cover the filing fee is enclosed.
- ☒ The Commissioner is hereby authorized to charge payment of the following fees associated with this communication or credit any overpayment to Deposit Account No. **50-0238**
A duplicate copy of this sheet is enclosed.
- ☒ Any additional filing fees required under 37 C.F.R. 1.16.
- ☒ Any patent application processing fees under 37 CFR 1.17.


SignatureDated: **January 21, 2003****ANDREW J. TELESZ, JR.**
REG. NO. 33,581**VOLENTINE FRANCOS, P.L.L.C.**
12200 SUNRISE VALLEY DRIVE, SUITE 150
RESTON, VA 20191**TEL. NO. (703) 715-0870**

I certify that this document and fee is being deposited on _____ with the U.S. Postal Service as first class mail under 37 C.F.R. 1.8 and is addressed to the Assistant Commissioner for Patents, Washington, D.C. 20231.

Signature of Person Mailing Correspondence_____
Typed or Printed Name of Person Mailing Correspondence

CC:



OKI.295

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re PATENT APPLICATION of

Katsuhito Sasaki

Group Art Unit: 2823

Serial No.: 10/052,244

Examiner: J. Garcia

Filed: January 23, 2002

For: METHOD OF MANUFACTURING LATERAL DOUBLE-DIFFUSED METAL
OXIDE SEMICONDUCTOR DEVICE

AMENDMENT

Honorable Assistant Commissioner for Patents
Washington, D.C. 20231

Date: January 21, 2003

Sir:

In response to the Office Action dated November 7, 2002, the following
amendments and remarks are respectfully submitted in connection with the above-
identified application.

In the Abstract:

Please cancel the Abstract and replace with the Abstract attached herewith.

In the Specification:

Replace the paragraph beginning on page 5, line 7 with the following paragraph:

Subsequently, a first insulating film 104 is formed on the semiconductor
substrate 101 of the first conductivity type, and a portion of the first insulating film 104
above the first diffusion layer 103 of the second conductivity type is opened (first

RECEIVED
JAN 24 2003
TECHNOLOGY CENTER 2800

7/A
1-30-03
Juni

A1